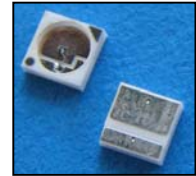




LED34-HIGH-SMD3



TECHNICAL DATA

Mid-Infrared Light Emitting Diode, SMD

Light Emitting Diodes with central wavelength 3.40 μm series are based on heterostructures grown on InAs substrates by MOCVD. InAs is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement. LED34-HIGH-SMD3 has a stable output power and a lifetime more than 80000 hours.

Features

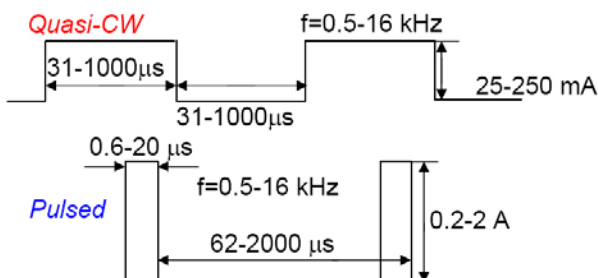
- Structure: InAsSb/InAsSbP
- Peak Wavelength: typ. 3.40 μm
- Optical Output Power: typ. 65 μW qCW
- Package: SMD 3x3 mm



Specifications

Item	Condition	Rating			Unit
		Min.	Typ.	Max.	
Peak Wavelength	T=300 K	3.30	3.40	3.49	μm
FWHM	150 mA CW	300	400	500	nm
Quasi-CW Optical Power	200 mA qCW	45	65	80	mW
Pulsed Optical Power	1 A	480	600	720	mW
Switching Time	T=300 K	10	20	30	ns
Operation Voltage	200 mA qCW				V
Operating Temperature		-240 ... +50			$^{\circ}\text{C}$
Emitting Area		300x300			μm
Soldering Temperature		180			$^{\circ}\text{C}$
Package	SMD type package 3x3 mm based on high thermal conductivity ceramics				

Operating Regime



Quasi-CW

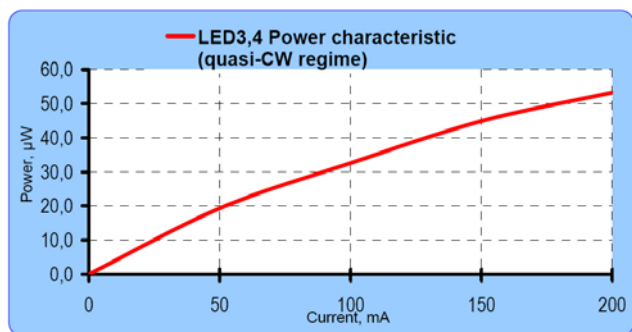
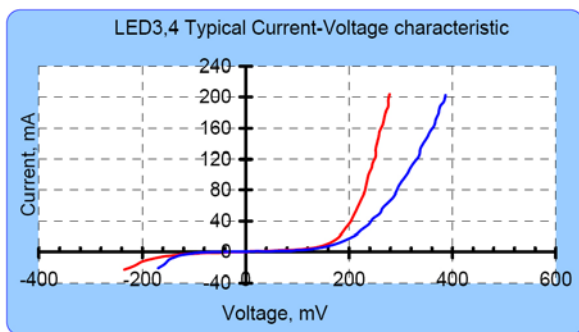
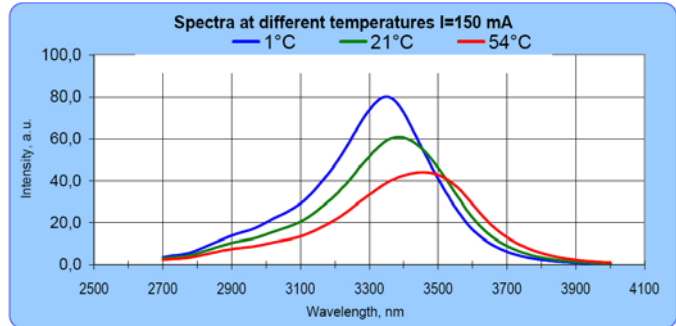
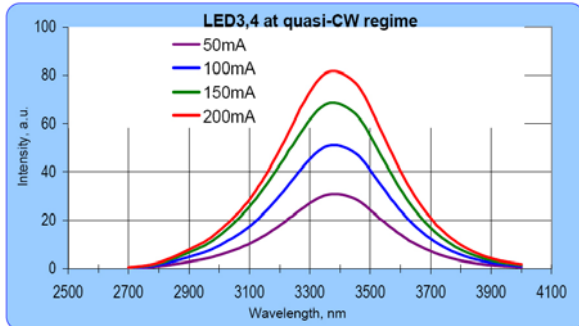
- Maximum current 220 mA
- Recommended current 150-200mA

Pulsed

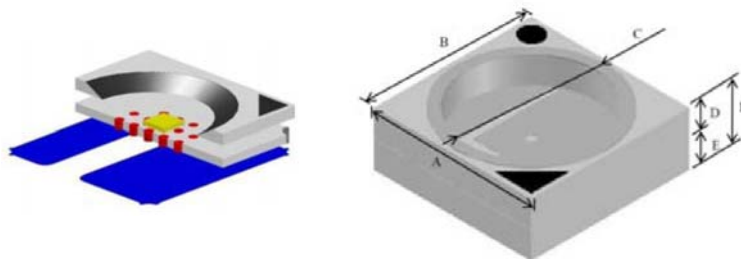
- Maximum current 1 A (puls length 500 ns, repetition rate 2kHz)



Typical Performance Curves



Package



ITEM	Symbol	Rule
Basic Outline	A	3.0 ± 0.1mm
Basic Outline	B	3.0 ± 0.1mm
Cavity size	C	Max 2.4Φ
Top layer	D	Min 0.4mm
Bottom layer	E	Min 0.4mm
Thickness	F	Max 2mm

- Tiny package for surface mounting
- Anode and cathode are led to the metalized areas on the back side of the ceramic surface
- Material – Low Temperature Co-fired Ceramic (LTCC):
 - thermal conductivity 25 W/mK
 - thermoresistance 8 °C/W